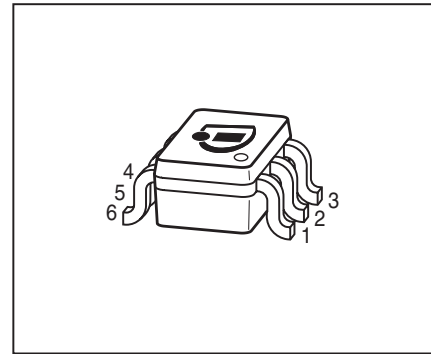
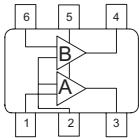


**DUAL N-Channel MOSFET Tetrode**

- Designed for input stages of 2 band tuners
- Two AGC amplifiers in one single package with on-chip internal switch
- Only one switching line to control both FETs
- Integrated gate protection diodes
- High gain, low noise figure, high AGC-range
- Good cross modulation at gain reduction
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Detailed functional diagram on page 4


**BG3430R**


**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

Type	Package	Pin Configuration						Marking
BG3430R	SOT363	1=G1*	2=S	3=D*	4=D**	5=G2	6=G1**	KNs

\* For amp. A; \*\* for amp. B

180° rotated tape loading orientation available

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	8	V
Continuous drain current	$I_D$	25	mA
Gate 1/ gate 2-source current	$\pm I_{G1/2SM}$	1	
Gate 1/ gate 2-source voltage	$\pm V_{G1/G2S}$	6	V
Total power dissipation	$P_{tot}$	200	mW
Storage temperature	$T_{stg}$	-55 ... 150	°C
Channel temperature	$T_{ch}$	150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Channel - soldering point <sup>1)</sup>	$R_{thchs}$	≤ 280	K/W

<sup>1</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

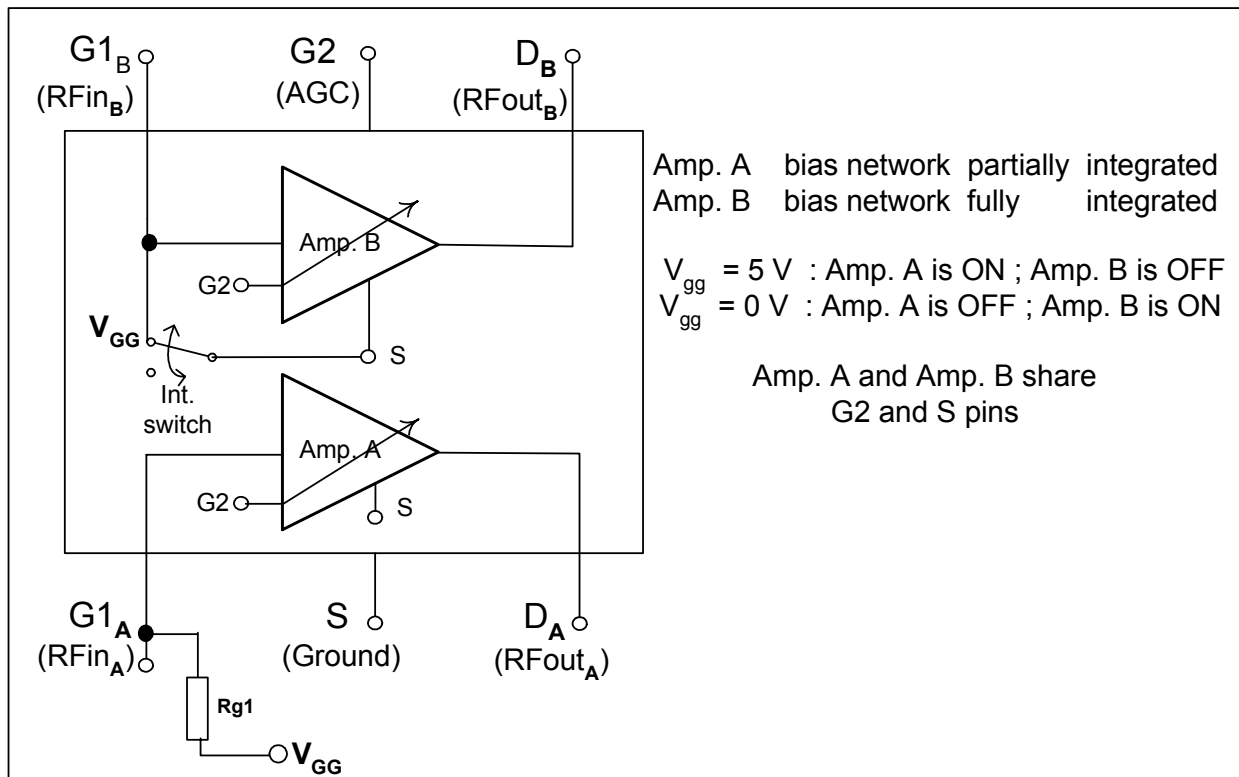
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Drain-source breakdown voltage $I_D = 100 \mu\text{A}$ , $V_{G1S} = 0 \text{ V}$ , $V_{G2S} = 0 \text{ V}$	$V_{(BR)DS}$	12	-	-	V
Gate1-source breakdown voltage $+I_{G1S} = 10 \text{ mA}$ , $V_{G2S} = 0 \text{ V}$ , $V_{DS} = 0 \text{ V}$	$+V_{(BR)G1SS}$	6	-	15	
Gate2-source breakdown voltage $+I_{G2S} = 10 \text{ mA}$ , $V_{G1S} = 0 \text{ V}$ , $V_{DS} = 0 \text{ V}$	$+V_{(BR)G2SS}$	6	-	15	
Gate1-source leakage current $V_{G1S} = 6 \text{ V}$ , $V_{G2S} = 0 \text{ V}$	$+I_{G1SS}$	-	-	5	$\mu\text{A}$
Gate2-source leakage current $V_{G2S} = 6 \text{ V}$ , $V_{G1S} = 0 \text{ V}$ , $V_{DS} = 0 \text{ V}$	$+I_{G2SS}$	-	-	50	nA
Drain current $V_{DS} = 5 \text{ V}$ , $V_{G1S} = 0 \text{ V}$ , $V_{G2S} = 4 \text{ V}$	$I_{DSS}$	-	-	100	$\mu\text{A}$
Operating current (selfbiased) $V_{DS} = 5 \text{ V}$ , $V_{G2S} = 4 \text{ V}$ , amp.B	$I_{DSO}$	-	13	-	mA
Drain-source current $V_{DS} = 5 \text{ V}$ , $V_{G2S} = 4 \text{ V}$ , $R_{G1} = 100 \text{ k}\Omega$ , amp. A	$I_{DSX}$	-	13	-	
Gate1-source pinch-off voltage $V_{DS} = 5 \text{ V}$ , $V_{G2S} = 4 \text{ V}$ , $I_D = 100 \mu\text{A}$	$V_{G1S(p)}$	-	0.5	-	V
Gate2-source pinch-off voltage $V_{DS} = 5 \text{ V}$ , $I_D = 100 \mu\text{A}$	$V_{G2S(p)}$	-	0.6	-	

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b> $V_{DS} = 5\text{V}$ , $V_{G2S} = 4\text{V}$ , ( $I_D = 14\text{ mA}$ ) (verified by random sampling)					
Forward transconductance	$g_{fs}$	-	33	-	mS
Gate1 input capacitance $f = 10\text{ MHz}$	$C_{g1ss}$	-	1.9	-	pF
Output capacitance $f = 10\text{ MHz}$	$C_{dss}$	-	1.3	-	
Power gain $f = 800\text{ MHz}$ $f = 45\text{ MHz}$	$G_p$	- -	25 33	- -	dB
Noise figure $f = 800\text{ MHz}$ $f = 45\text{ MHz}$	$F$	- -	1.3 1	- -	dB
Gain control range $V_{G2S} = 4 \dots 0\text{ V}$ , $f = 800\text{ MHz}$	$\Delta G_p$	45	-	-	
Cross-modulation $k=1\%$ , $f_w=50\text{MHz}$ , $f_{unw}=60\text{MHz}$ AGC = 0 dB AGC = 10 dB AGC = 40 dB	$X_{mod}$	90 - -	- 93 105	- - -	-

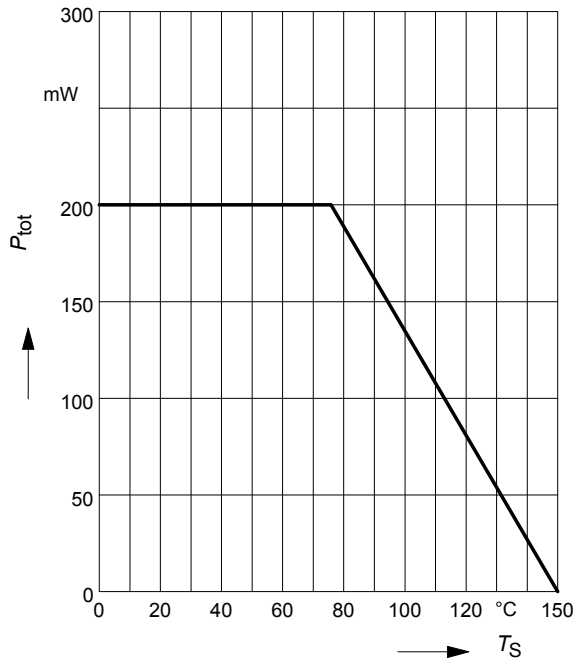
**Functional diagram**

a) shows pinning of BG3430R.

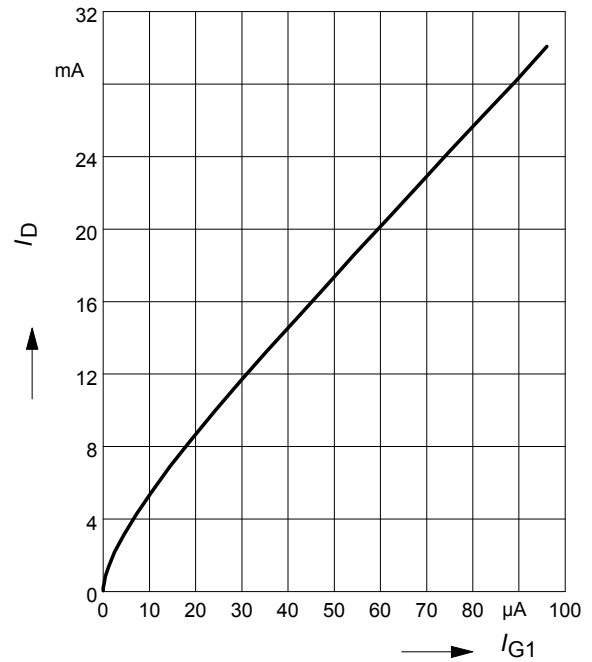


**Total power dissipation  $P_{tot} = f(T_S)$** 

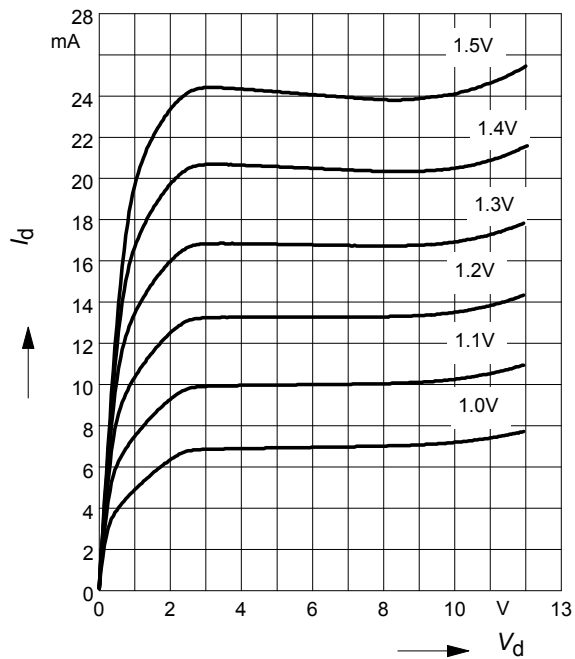
amp. A = amp. B


**Drain current  $I_D = f(I_{G1})$** 
 $V_{G2S} = 4V$ 

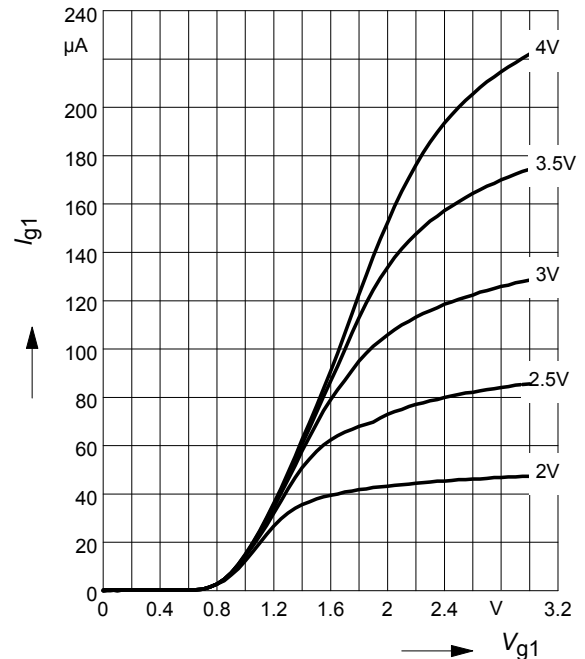
amp. A


**Output characteristics  $I_D = f(V_{DS})$** 

amp. A = amp. B

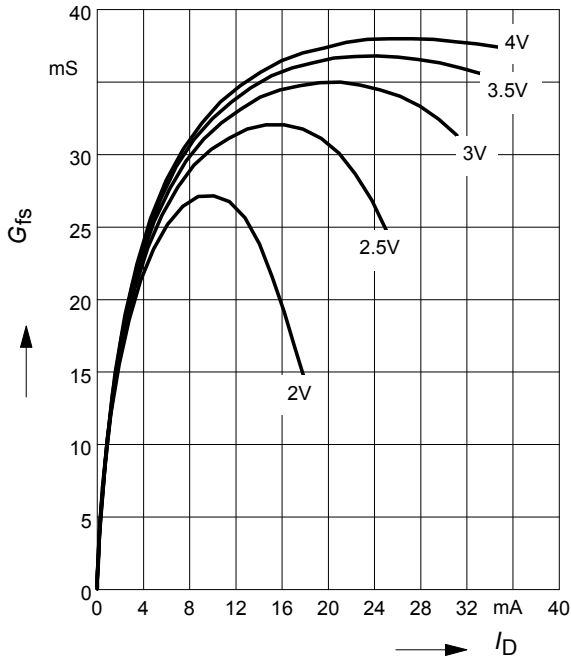

**Gate 1 current  $I_{G1} = f(V_{G1S})$** 
 $V_{DS} = 5V, V_{G2S} = \text{Parameter}$ 

amp. A

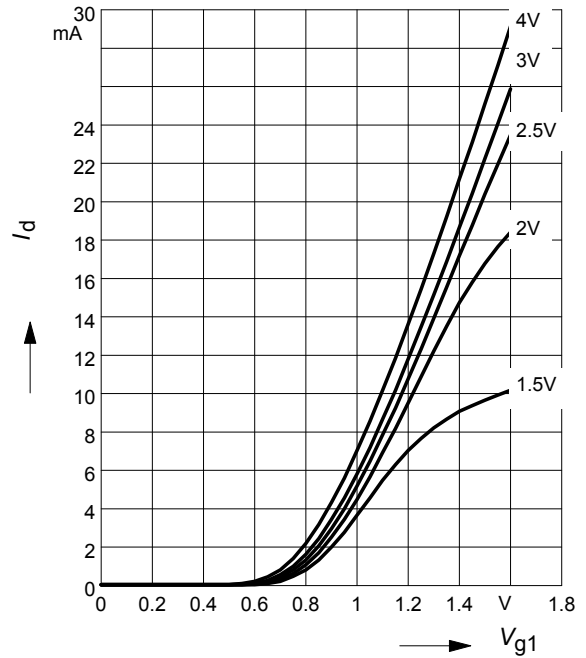


**Gate 1 forward transconductance**

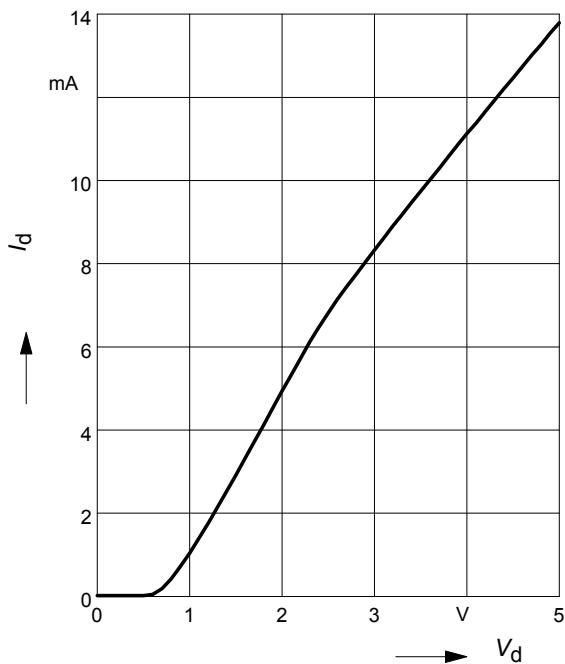
$g_{fs} = f(I_D)$ ,  $V_{DS} = 5V$ ,  $V_{G2S} = \text{Parameter}$   
 amp. A = amp. B


**Drain current  $I_D = f(V_{G1S})$** 

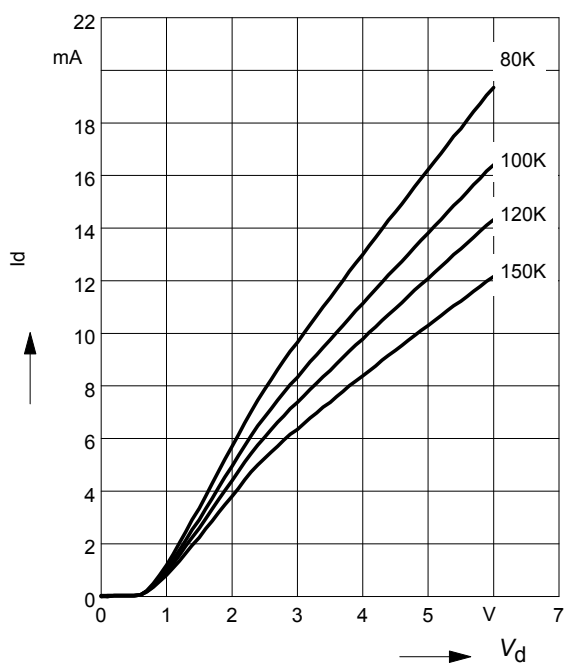
$V_{DS} = 5V$ ,  $V_{G2S} = \text{Parameter}$   
 amp. A = amp. B

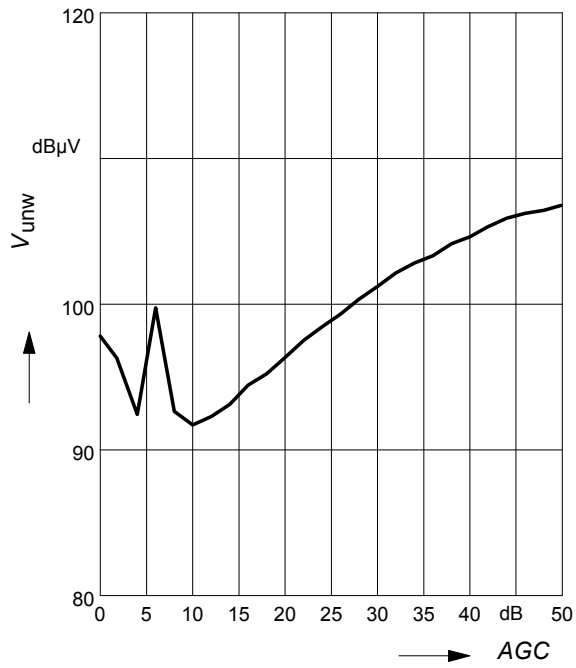

**Drain current  $I_D = f(V_{GG})$  amp.A**

$V_{DS} = 5V$ ,  $V_{G2S} = 4V$ ,  $R_{G1} = 100k\Omega$   
 (connected to  $V_{GG}$ ,  $V_{GG} = \text{gate1 supply voltage}$ )

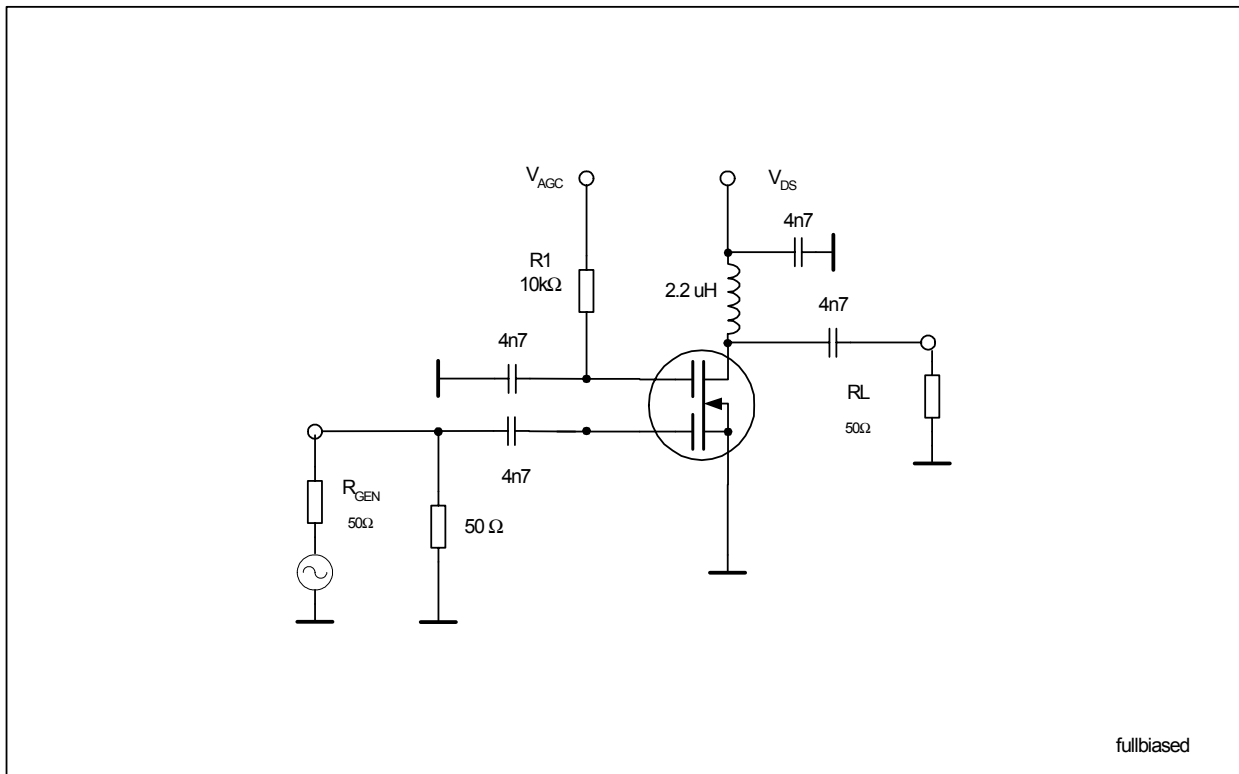
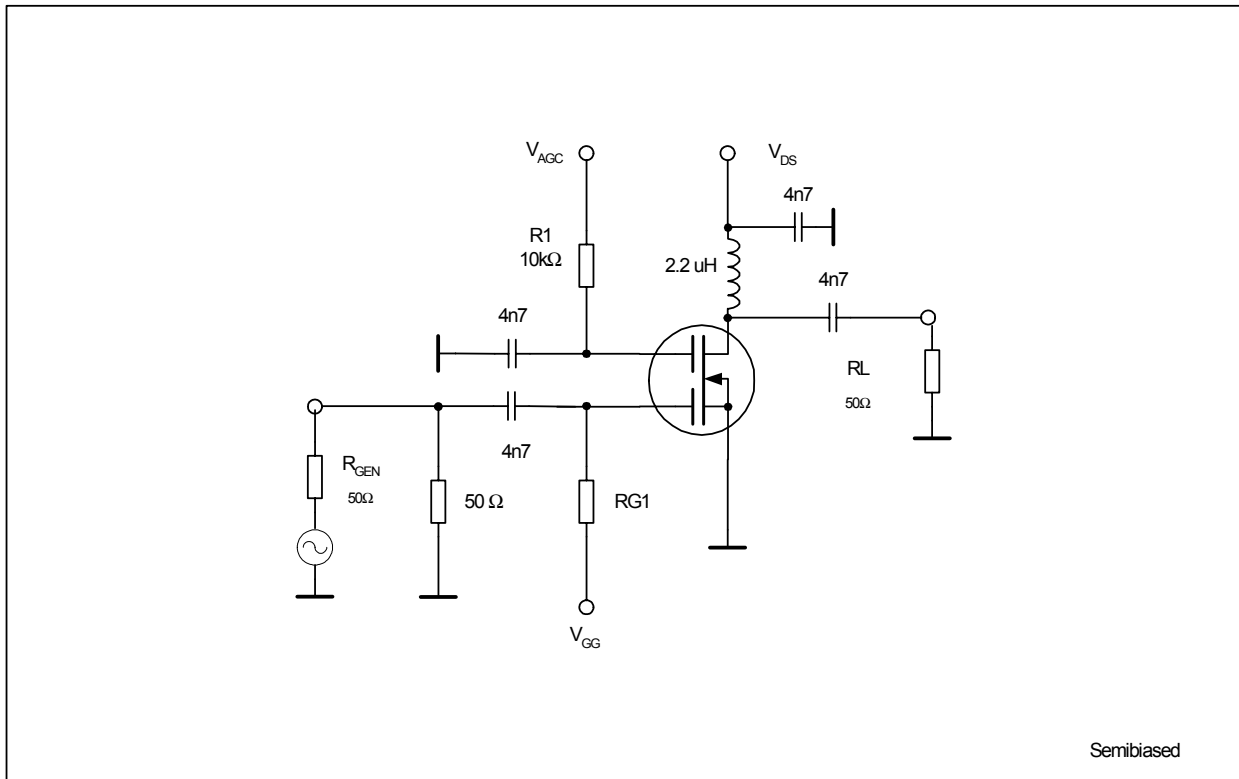

**Drain current  $I_D = f(V_{GG})$** 

$V_{G2S} = 4V$ ,  $R_{G1} = \text{Parameter}$  in  $k\Omega$   
 amp. A

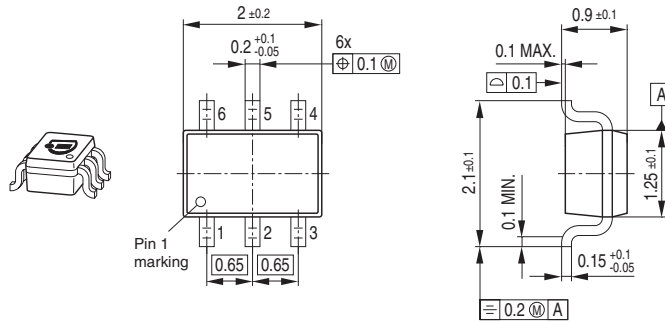


**Crossmodulation  $V_{unw} = (AGC)$** 
 $V_{DS} = 5 \text{ V}$ , amp. A = amp. B


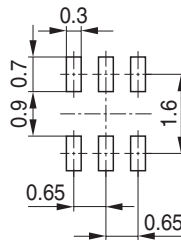


**Crossmodulation test circuit**


Package Outline

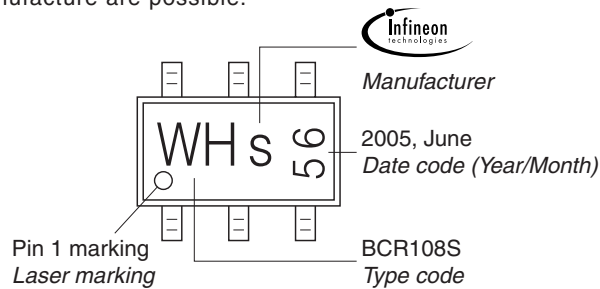


Foot Print



Marking Layout (Example)

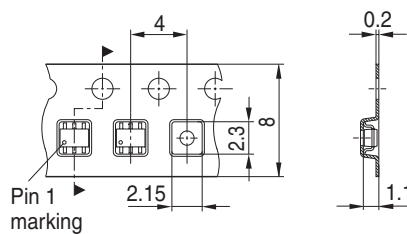
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel  $\phi$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\phi$ 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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